

# Specification

## Scope

The equipment under test is a dual sim-card Three module quad band smart phone. This document is shown and provided the more detail information about the platform used in. The basic description for the Baseband and RF section are also included.

## PMU

[MT6762V](#) is a power management system chip optimized for 3G/4G, especially based on the Spreadtrum [MT6762V](#) system solution. [MT6762V](#) integrated 7 DC-DCs and 26 low dropout regulators (LDOs), which are optimized for specific 3G subsystems. All the chip in the platform power through this chip. Support standby mode with small deep-sleep current.

## Baseband

[MT6762V](#) is a highly integrated application processor with embedded TD-LTE, LTE FDD, TD-SCDMA/HSPA(+), WCDMA/DC-HSDPA. It consists of Dual-core ARM Cortex TM -A75 processor and Six-core ARM Cortex TM -A55 processor as application processor, which includes a NEON multimedia processing engine, ARM Mali [MT6762V](#) as 3D graphics accelerator, multi-standard multi-media accelerators and advanced audio subsystem. The specially optimized architecture of [MT6762V](#) can achieve high performance and low power for a lot of applications. Proprietary architectures and algorithms were developed for low power ASIC design and power management. Unique techniques are used for noise suppression/cancellation, echo suppression/cancellation algorithm. Overall, UMS512 chip set presents a high cost-effective platform for six mode Android mobile devices.

The multi-standard video accelerator and an advanced audio subsystem are also included to provide advanced multimedia application and services such as streaming Audio and video, a multitude of decoders and encoders such as H.264 and MPEG-4. Audio supported includes FR, HR, EFR, AMR FR, and AMR HR vocoders, polyphonic ringtones and advanced audio functions such as echo cancellation, hands-free speakerphone operation and noise cancellation.

## WCN

[MT6631N](#) is a chip that includes the WiFi baseband core and their RF. It's the highest level of integration for a mobile system with integrated [802.11b/g/n](#) and single stream 802.11n, Smart ready mode, It also includes on-chip [2.4GHz](#) CMOS power amplifiers.

Implemented advanced power saving technology, the chip can satisfy the mobile devices which require minimal power consumption and compact PCB size.

## RF

[MT6762V](#) is a highly integrated, single-die radio transceiver chip that supports 3G WCDMA, HSDPA, HSUPA. Implemented in low cost bulk CMOS, it is optimized to meet the challenges of today's small form factor, power efficient, high performance cellular handsets. The [MT6762V](#) has total of 7 single-ended transmit ports, 12 primary and 12 diversity single-ended receive ports. The [MT6762V](#) provides connectivity multiple bands of operation. The [MT6762V](#) offers a cost competitive and small footprint radio solution for multi-mode, multi-band applications with the highest performance at the lowest power.

The linear transceiver architecture of [MT6762V](#) is utilized for 3G systems, offering excellent performance and design margins over 3GPP requirements.

## PA

The [MT6762V](#) is a multi-mode multi-band front-end module (FEM) delivering both the power amplification and antenna switching functions. With the state-of-the-art integration

design and advanced GaAs technology, this FEM supports both quad-band. The [MT6762V](#) is a 42-pin power amplifier module developed for high linearity applications. With advanced InGaP HBT technology, the module supports multi-band WCDMA&TD-SCDMA&FDD-LTE&TDD-LTE application, including WCDMA Band5, FDD-LTE Band5, TDD-LTE Band 41

. The SPM6743-11 meets the stringent linearity requirements of LTE QPSK specifications, as well as those of 16QAM modulation.

The [MT6762V](#) is self contained with three GaAs power amplifiers for low, mid and high bands, a CMOS controller, a SOI 3P4T switch, a SP5T switch ,a SP7T switch and input & output matching networks. The GaAs PA provides RF amplification in linear mode, while the CMOS controller provides regulated voltage through MIPI RFFE interface.

The integrated SOI switch supports band selection and Tx/Rx function. The module is fully matched to 50 ohms at all RF ports.

BT:

VT10M2 Tablet PC uses [MT6631N](#) chip and Bluetooth V5.0. The whole Bluetooth protocol architecture can be divided into three parts: the bottom hardware module, the middle protocol layer and the high-end application layer. The external circuit consists of antenna RF matching circuit, power filter circuit and output circuit, KEY function key PIO circuit and LED indicator lamp

#### **Operating Frequency Band (RF):**

Bluetooth: 2402-2480MHz

WiFi: IEEE 802.11b/g/n 20: 2412-2462MHz/ 11 channel

IEEE 802.11n 40: 2422-2452MHz/ 7 channel

IEEE 802.11a/n/ac(20M): 5150MHz ~5250MHz/ 4 channel

IEEE 802.11n/ac(40M): 5150MHz ~5250MHz/ 2 channel

IEEE 802.11ac(80M): 5150MHz ~5250MHz/ 1 channel

IEEE 802.11a/n/ac(20M): 5250MHz ~5350 MHz/ 4 channel

IEEE802.11n/ac(40M): 5250MHz ~5350 MHz/ 2 channel

IEEE802.11ac(80M): 5250MHz ~5350 MHz/ 1 channel

IEEE 802.11a/n/ac(20M): 5470MHz ~5725 MHz/ 11 channel

IEEE802.11n/ac(40M): 5470MHz ~5725 MHz/ 5 channel

IEEE802.11ac(80M): 5470MHz ~5725 MHz/ 3 channel

IEEE 802.11a/n/ac(20M): 5725MHz ~5850MHz/ 5 channel

IEEE 802.11n/ac(40M): 5725MHz ~5850MHz/ 2 channel

IEEE 802.11ac(80M): 5725MHz ~5850MHz/ 1 channel

GSM/GPRS/EDGE 850: 824~849MHz

GSM/GPRS/EDGE 1900: 1850~1910MHz

WCDMA Band 5: 824~849MHz

WCDMA Band 4: 1710~1755MHz

WCDMA Band 2: 1850~1910MHz

FDD-LTE BAND 2:1850-1910MHz

FDD-LTE BAND 4:1710-1755MHz

FDD-LTE BAND 5: 824-849MHz

FDD-LTE BAND 12: 699-716MHz

FDD-LTE BAND 17: 704-716MHz

FDD-LTE BAND 25: 1850-1915MHz

FDD-LTE BAND 26: 814-849MHz

TDD-LTE BAND 41: 2496-2690 MHz

FDD-LTE BAND 66: 1710-1780MHz

TDD-LTE BAND 71: 663-702MHz

**Modulation mode:**

Bluetooth: GFSK,  $\pi/4$  DQPSK, 8DPSK

WiFi: DSSS, OFDM, CCK

2/3G: GMSK, BPSK

LTE: QPSK, 16QAM

**Maximum of Antenna Gain:**

Bluetooth: 0.89dBi

WiFi (2.4G) : 0.89dBi

WiFi (5.2G) : -0.48dBi

WiFi (5.3G) : -1.43dBi

WiFi (5.6G) : 0.09dBi

WiFi (5.8G) : -1.23dBi

GSM850: -7.64dBi,

GSM1900: -1.06dBi

WCDMA Band 5: -7.64dBi

WCDMA Band 4: -0.1dBi

WCDMA Band 2: -1.06dBi

FDD-LTE BAND 2: -1.06dBi

FDD-LTE BAND 4: -0.1dBi

FDD-LTE BAND 5: -7.64dBi

FDD-LTE BAND 12: -6.56 dBi

FDD-LTE BAND 17: -6.56dBi

FDD-LTE BAND 25: -1.06 dBi

FDD-LTE BAND 26: -7.64dBi

TDD-LTE BAND 41: -0.36dBi

FDD-LTE BAND 66: -0.1dBi

TDD-LTE BAND 71: -4.82dBi

**Ratings:**

DC 5V charging from adapter

DC 3.8V by battery